

FEB 17 2004

**TRANSMITTAL LETTER
(General - Patent Pending)**

Docket No.
112857-315

In Re Application Of: **Yoshiyuki Yanagisawa et al.**

Serial No. 10/062,776	Filing Date 01/30/02	Examiner Savitri Mulpuri	Group Art Unit 2812
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Title: **DEVICE TRANSFER METHOD AND PANEL**

TO THE COMMISSIONER FOR PATENTS:

Transmitted herewith is:

Request for Continued Examination (RCE) Transmittal (Duplicate); Transmittal of Information Disclosure Statement (Duplicate); Information Disclosure Statement (4 Pages); PTO Form 1449 (3 Pages); Cited References (67 Cited References); Check in the Amount of \$770.00; and Return Receipt Postcard.

in the above identified application.

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Dated: February 12, 2004

**Jeffrey H. Canfield, Esq. (38,404)
Bell, Boyd & Lloyd LLC
P.O. Box 1135
Chicago, Illinois 60690-1135
Telephone: (312) 807-4233**

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TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
112857-315

In Re Application Of: **Yoshiyuki Yanagisawa et al.**

Serial No.	Filing Date	Examiner	Group Art Unit
10/062,776	01/30/2002	Savitri Mulpuri	2812

Title: **DEVICE TRANSFER METHOD AND PANEL**

FEB 17 2004

Address to:

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

37 CFR 1.97(b)

1. The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.

37 CFR 1.97(c)

2. The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:
- the statement specified in 37 CFR 1.97(e);
- OR**
- the fee set forth in 37 CFR 1.17(p).

TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT
(Under 37 CFR 1.97(b) or 1.97(c))

Docket No.
112857-315

In Re Application: Yoshiyuki Yanagisawa et al.

Serial No.

10/062,776

Filing Date

01/30/2002

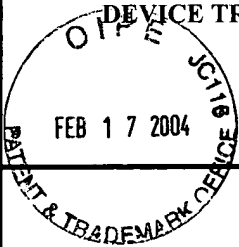
Examiner

Savitri Mulpuri

Group Art Unit

2812

DEVICE TRANSFER METHOD AND PANEL



Payment of Fee

(Only complete if Applicant elects to pay the fee set forth in 37 CFR 1.17(p))

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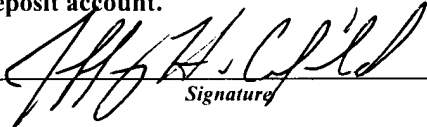
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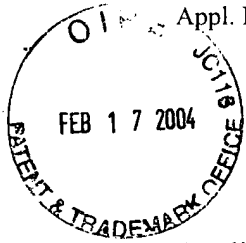
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Dated: February 12, 2004

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Telephone: (312) 807-4233

CC:



Appl. No. 10/062,776

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yoshiyuki Yanagisawa et al.
Appl. No.: 10/062,776
Conf. No.: 3355
Filed: January 30, 2002
Title: DEVICE TRANSFER METHOD AND PANEL
Art Unit: 2812
Examiner: Savitri Mulpuri
Docket No.: 112857-315

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 37 C.F.R. 1.97, and 37 C.F.R. 1.98, Applicants request that a citation and examination of the references cited below, and on the attached PTO-1449 form, copies of which are enclosed, be made during the course of examination of the above/identified application for United States patent.

U.S. PATENT DOCUMENTS

<u>Document No.</u>	<u>Date</u>	<u>Inventor</u>
5,177,405	01/05/1993	Kusuda et al.
5,206,749	04/27/1993	Zavracky et al.
5,258,320	11/02/1993	Zavracky et al.
5,438,241	08/01/1995	Zavracky et al.
5,739,800	04/14/1998	Lebby et al.
5,981,977	11/09/1999	Furukawa et al.

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<u>Document No.</u>	<u>Date</u>	<u>Country</u>
56-17385	02/19/1981	Japan
56-92577	07/27/1981	Japan
57-45583	03/15/1982	Japan
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Kapolnek et al., *Spatial control of InGaN luminescence by MOCVD selective epitaxy*, Journal of Crystal Growth, 189/190 (1998) pp. 83/86.

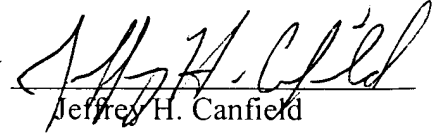
Applied Physics Letters, Vol. 76, Number 22, 29 May 2000, "*Selective growth of InGaN quantum dot structures and their microphotoluminescence at room temperature*", Tachibani et al, pages 3212/3214

Applicants look forward to early and favorable consideration of this matter.

Respectfully submitted,

BELL, BOYD & LLOYD LLC

BY



Jeffrey H. Canfield

Reg. No.38,404

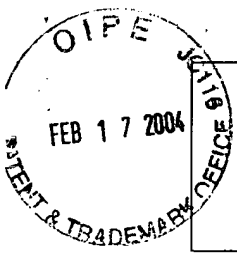
P.O. Box 1135

Chicago, Illinois 60690-1135

Phone: (312) 807-4233

Dated: February 12, 2004





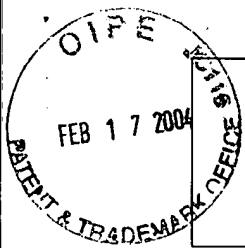
INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary) PTO Form 1449	Atty Docket No. 112857-315	Application No. 10/062,776
	Applicant Yoshiyuki Yanagisawa et al.	
	Filing Date 01/30/2002	Group 2812

U.S. PATENT DOCUMENTS						
Examiner's Initials	Document Number	Publication Date	Inventor	Class	Subclass	Filing Date If Appropriate
	5,177,405	01/05/1993	Kusuda et al.			
	5,206,749	04/27/1993	Zavracky et al.			
	5,258,320	11/02/1993	Zavracky et al.			
	5,438,241	08/01/1995	Zavracky et al.			
	5,739,800	04/14/1998	Lebby et al.			
	5,981,977	11/09/1999	Furukawa et al.			

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						Yes	No
	56-17385 ✓	02/19/1981	Japan				
	56-92577 ✓	07/27/1981	Japan				
	57-45583 ✓	03/15/1982	Japan				
	57-52071 ✓	03/27/1982	Japan				
	57-52072 ✓	03/27/1982	Japan				
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	6-45648	02/18/1994	Japan				
	06-067044	03/11/1994	Japan				
	06-504139	05/12/1994	Japan				

Examiner:	Date Considered:
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**INFORMATION DISCLOSURE CITATION
IN AN APPLICATION**
(Use several sheets if necessary)

PTO Form 1449

Atty Docket No. 112857-315	Application No. 10/062,776
Applicant Yoshiyuki Yanagisawa et al.	
Filing Date 01/30/2002	Group 2812

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	07-199829	04/08/1995	Japan				
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	2002-185660	12/12/2002	Japan					

Examiner's Initials	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
	Zheleva et al., "Pendeo/Epitaxy - A New Approach For Lateral Growth Of Gallium Nitride Structures", MRS Internet J. Nitride Semicond. Res. 4S1, G3.38 (1999).
	Kapolnek et al., "Spatial Control Of InGaN Luminescence By MOCVD Selective Epitaxy, Journal Of Crystal Growth", 189/190 (1998) pp. 83/86.
	Applied Physics Letters, Vol. 76, Number 22, 29 May 2000, "Selective Growth Of InGaN Quantum Dot Structures And Their Microphotoluminescence At Room Temperature", Tachibani et al, pages 3212/3214

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